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Vishay Siliconix

## Automotive N-Channel 60 V (D-S) 175 °C MOSFET



| PRODUCT SUMMARY                                  |                |  |  |  |
|--|----------------|--|--|--|
| V <sub>DS</sub> (V)                              | 60             |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$  | 0.0030         |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$ | 0.0047         |  |  |  |
| I <sub>D</sub> (A)                               | 278            |  |  |  |
| Configuration                                    | Single         |  |  |  |
| Package  | PowerPAK SO-8L |  |  |  |

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



|                  | O <sup>D</sup> |
|------------------|----------------|
| <del> -</del>    | <b>-</b>       |
| G O              |                |
| N-Channel MOSFET | o <sub>s</sub> |

| ABSOLUTE MAXIMUM RATINGS                                  | (T <sub>C</sub> = 25 °C, unles | s otherwise noted                 | 1)          |    |  |
|---|--------------------------------|-----------------------------------|-------------|----|--|
| PARAMETER   | SYMBOL                         | LIMIT                             | UNIT        |    |  |
| Drain-source voltage                                      |                                | V <sub>DS</sub>                   | 60          | V  |  |
| Gate-source voltage                                       |                                | $V_{GS}$                          | ± 20        | V  |  |
| Continuous drain current                                  | T <sub>C</sub> = 25 °C a       | 1                                 | 278         |    |  |
|   | T <sub>C</sub> = 125 °C        | - I <sub>D</sub>                  | 166         |    |  |
| Continuous source current (diode conduction) a            |                                | I <sub>S</sub>                    | 454         | Α  |  |
| Pulsed drain current b                                    |                                | I <sub>DM</sub>                   | 575         |    |  |
| Single pulse avalanche current                            | L = 0.1 mH                     | l <sub>AS</sub>                   | 48          |    |  |
| Single pulse avalanche energy                             | L = U.1 IIII                   | E <sub>AS</sub>                   | 115         | mJ |  |
| Maximum naver dissination                                 | T <sub>C</sub> = 25 °C         | D                                 | 500         | W  |  |
| Maximum power dissipation                                 | T <sub>C</sub> = 125 °C        | $P_{D}$                           | 166         | VV |  |
| Operating junction and storage temperature range          |                                | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175 | °C |  |
| Soldering recommendations (peak temperature) <sup>d</sup> |                                |                                   | 260         | C  |  |

| THERMAL RESISTANCE RATINGS |             |            |       |      |
|----------------------------|-------------|------------|-------|------|
| PARAMETER                  |             | SYMBOL     | LIMIT | UNIT |
| Junction-to-ambient        | PCB mount c | $R_{thJA}$ | 42    | °C/W |
| Junction-to-case (drain)   |             | $R_{thJC}$ | 0.30  | C/VV |

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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| PARAMETER                                | SYMBOL                   | TES   | T CONDITIONS                                    | MIN. | TYP.   | MAX.    | UNIT |
|--|--------------------------|---|---|------|--------|---------|------|
| Static                                   | •                        |   |   | l    |        | •       |      |
| Drain-source breakdown voltage           | $V_{DS}$                 | V <sub>GS</sub>                                   | = 0, I <sub>D</sub> = 250 μA                    | 60   | -      | -       | V    |
| Gate-source threshold voltage            | V <sub>GS(th)</sub>      | V <sub>DS</sub> =                                 | · V <sub>GS</sub> , I <sub>D</sub> = 250 μA     | 1.5  | 2.0    | 2.5     | V    |
| Gate-source leakage                      | I <sub>GSS</sub>         | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ |   | -    | -      | ± 100   | nA   |
|  |                          | $V_{GS} = 0 V$                                    | V <sub>DS</sub> = 60 V                          | -    | -      | 1       |      |
| Zero gate voltage drain current          | I <sub>DSS</sub>         | V <sub>GS</sub> = 0 V                             | V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C | -    | -      | 50      | μΑ   |
|  |                          | V <sub>GS</sub> = 0 V                             | V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C | -    | -      | 250     |      |
| On-state drain current <sup>a</sup>      | I <sub>D(on)</sub>       | V <sub>GS</sub> = 10 V                            | $V_{DS} \ge 5 \text{ V}$                        | 30   | -      | -       | Α    |
|  |                          | V <sub>GS</sub> = 10 V                            | I <sub>D</sub> = 15 A                           | -    | 0.0026 | 0.0030  |      |
| Duning anyone are state unalistance 2    |                          | V <sub>GS</sub> = 10 V                            | I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C  | -    | -      | 0.00516 | 0    |
| Drain-source on-state resistance a       | R <sub>DS(on)</sub>      | V <sub>GS</sub> = 10 V                            | I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C  | -    | -      | 0.0065  | Ω    |
|  |                          | V <sub>GS</sub> = 4.5 V                           | I <sub>D</sub> = 15 A                           | -    | 0.0036 | 0.0047  |      |
| Forward transconductance b               | 9 <sub>fs</sub>          | V <sub>DS</sub>                                   | = 15 V, I <sub>D</sub> = 10 A                   | -    | 75     | -       | S    |
| Dynamic <sup>b</sup>                     |                          |   |   |      | •      | •       |      |
| Input capacitance                        | C <sub>iss</sub>         |   |   | -    | 3915   | 5485    |      |
| Output capacitance                       | C <sub>oss</sub>         | $V_{GS} = 0 V$                                    | V <sub>DS</sub> = 25 V, f = 1 MHz               | -    | 1780   | 2500    | рF   |
| Reverse transfer capacitance             | C <sub>rss</sub>         |   |   | -    | 65     | 95      |      |
| Total gate charge <sup>c</sup>           | Qg                       |   |   | -    | 56     | 84      |      |
| Gate-source charge c                     | $Q_{gs}$                 | V <sub>GS</sub> = 10 V                            | $V_{DS} = 30 \text{ V}, I_{D} = 10 \text{ A}$   | -    | 13     | -       | nC   |
| Gate-drain charge c                      | Q <sub>gd</sub>          |   |   | -    | 5      | -       |      |
| Gate resistance                          | Rg                       |   | f = 1 MHz                                       | 0.6  | 1.3    | 2.0     | Ω    |
| Turn-on delay time <sup>c</sup>          | t <sub>d(on)</sub>       |   |   | -    | 13     | 20      |      |
| Rise time <sup>c</sup>                   | t <sub>r</sub>           | V <sub>DD</sub> =                                 | = 30 V, $R_L = 3.0 \Omega$                      | -    | 4      | 6       |      |
| Turn-off delay time <sup>c</sup>         | t <sub>d(off)</sub>      | $I_D \cong 10 A$ ,                                | $V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$        | -    | 34     | 50      | ns   |
| Fall time <sup>c</sup>                   | t <sub>f</sub>           |   |   | -    | 6      | 9       |      |
| Source-Drain Diode Ratings and Chara     | acteristics <sup>b</sup> |   |   |      |        |         |      |
| Pulsed current <sup>a</sup>              | I <sub>SM</sub>          |   |   | -    | -      | 575     | Α    |
| Forward voltage                          | V <sub>SD</sub>          | I <sub>F</sub> =                                  | 15 A, V <sub>GS</sub> = 0 V                     | -    | -      | 1.1     | V    |
| Body diode reverse recovery time         | t <sub>rr</sub>          |   |   | -    | 54     | 108     | ns   |
| Body diode reverse recovery charge       | Q <sub>rr</sub>          | ] , ,   | ۸ ما:/م <del>اد</del> ۱۰۰۰ ۸/۰۰۰                | -    | 64     | 128     | nC   |
| Reverse recovery fall time               | ta                       | - I <sub>F</sub> = 8 A, di/dt = 100 A/μs          |   | -    | 26     | -       |      |
| Reverse recovery rise time               | t <sub>b</sub>           |   |   | -    | 30     | -       | ns   |
| Body diode peak reverse recovery current | I <sub>RM(REC)</sub>     |   |   | -    | 2.0    | -       | Α    |

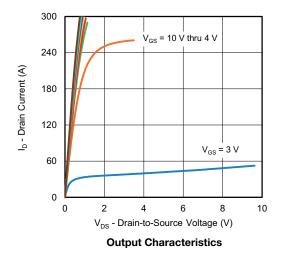
#### Notes

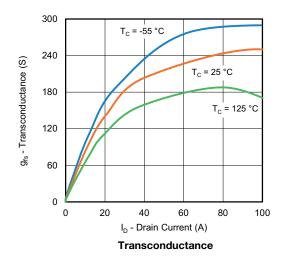
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

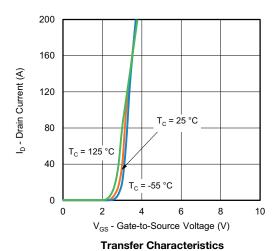
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

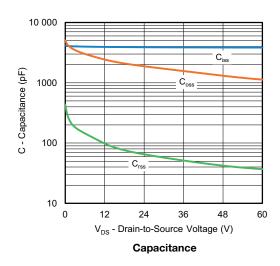


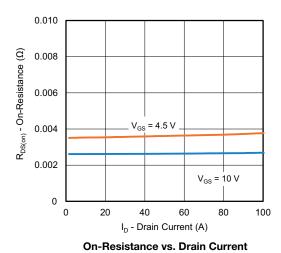
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

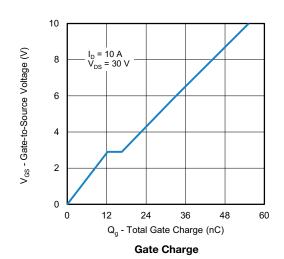






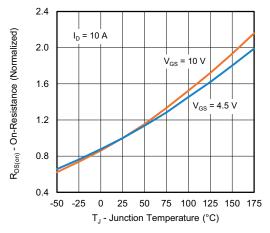




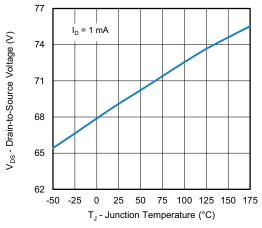




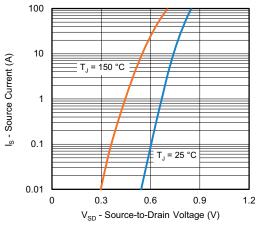
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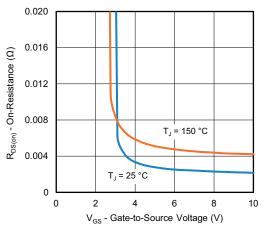
On-Resistance vs. Junction Temperature



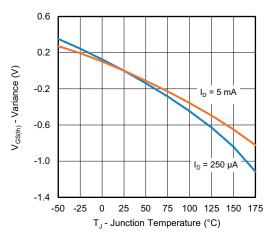
Drain Source Breakdown vs. Junction Temperature



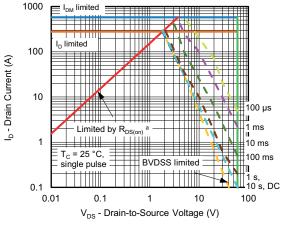
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to Source Voltage



Threshold Voltage



Safe Operating Area

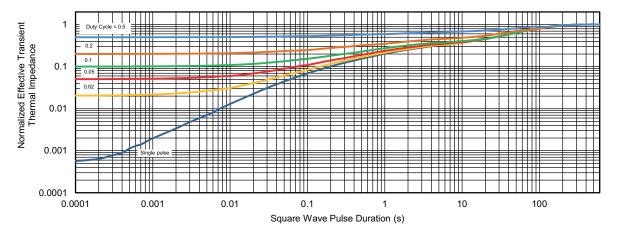
#### Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

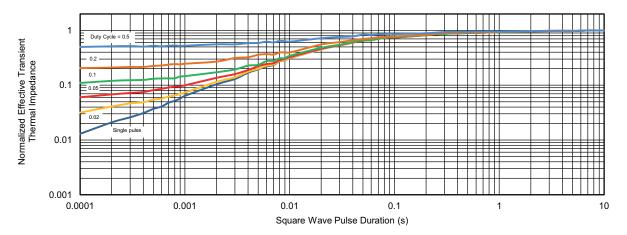
For technical questions, contact: automostechsu



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

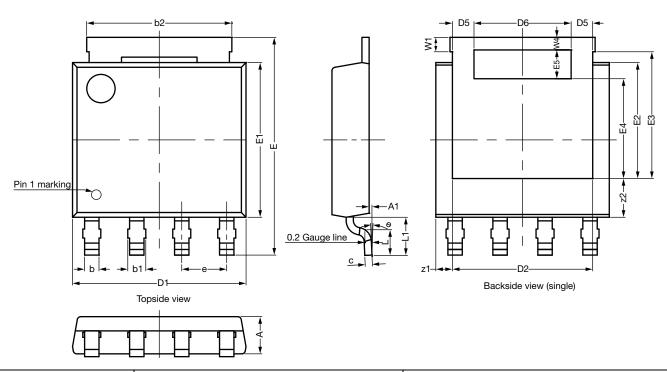


Normalized Thermal Transient Impedance, Junction-to-Case

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# PowerPAK® SO-8L (PPKSO8LWLA) Case Outline 3



| DIM. |      | MILLIMETERS |       |           | INCHES |       |  |  |
|------|------|-------------|-------|-----------|--------|-------|--|--|
|      | MIN. | NOM.        | MAX.  | MIN.      | NOM.   | MAX.  |  |  |
| Α    | 1.00 | 1.05        | 1.10  | 0.039     | 0.041  | 0.043 |  |  |
| A1   | 0.00 |             | 0.127 | 0.000     |        | 0.005 |  |  |
| b    | 0.33 | 0.41        | 0.49  | 0.013     | 0.016  | 0.019 |  |  |
| b1   | 0.43 | 0.51        | 0.59  | 0.017     | 0.020  | 0.023 |  |  |
| b2   | 4.00 | 4.10        | 4.20  | 0.157     | 0.161  | 0.165 |  |  |
| С    | 0.15 | 0.20        | 0.25  | 0.006     | 0.008  | 0.010 |  |  |
| D1   | 4.80 | 4.90        | 5.00  | 0.189     | 0.193  | 0.197 |  |  |
| D2   | 3.86 | 3.96        | 4.06  | 0.152     | 0.156  | 0.160 |  |  |
| D5   | 0.51 | 0.61        | 0.71  | 0.020     | 0.024  | 0.028 |  |  |
| D6   | 2.64 | 2.74        | 2.84  | 0.104     | 0.108  | 0.112 |  |  |
| е    |      | 1.27 BSC    |       | 0.050 BSC |        |       |  |  |
| E    | 6.05 | 6.15        | 6.25  | 0.238     | 0.242  | 0.246 |  |  |
| E1   | 4.27 | 4.37        | 4.47  | 0.168     | 0.172  | 0.176 |  |  |
| E2   | 3.18 | 3.28        | 3.38  | 0.125     | 0.129  | 0.133 |  |  |
| E3   | 3.48 | 3.58        | 3.68  | 0.137     | 0.141  | 0.145 |  |  |
| E4   | 2.72 | 2.82        | 2.92  | 0.107     | 0.111  | 0.115 |  |  |
| E5   | 0.71 | 0.81        | 0.91  | 0.028     | 0.032  | 0.036 |  |  |
| L    | 0.62 | 0.72        | 0.82  | 0.024     | 0.028  | 0.032 |  |  |
| L1   | 0.92 | 1.07        | 1.22  | 0.036     | 0.042  | 0.048 |  |  |
| W1   | 0.31 | 0.41        | 0.51  | 0.012     | 0.016  | 0.020 |  |  |
| W4   | 0.31 | 0.36        | 0.41  | 0.012     | 0.014  | 0.016 |  |  |
| z1   | 0.37 | 0.47        | 0.57  | 0.015     | 0.019  | 0.022 |  |  |
| z2   | 0.99 | 1.09        | 1.19  | 0.039     | 0.043  | 0.047 |  |  |
| θ    | 0°   |             | 5°    | 0°        |        | 5°    |  |  |

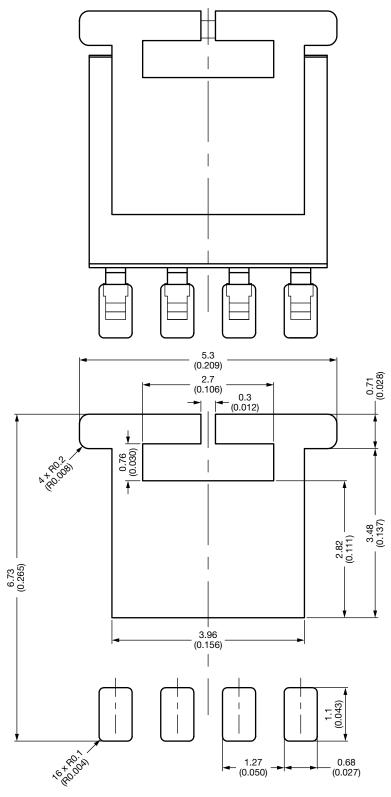
#### Note

• Millimeter will govern

Revison: 18-Sep-2023 1 Document Number: 76666



# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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